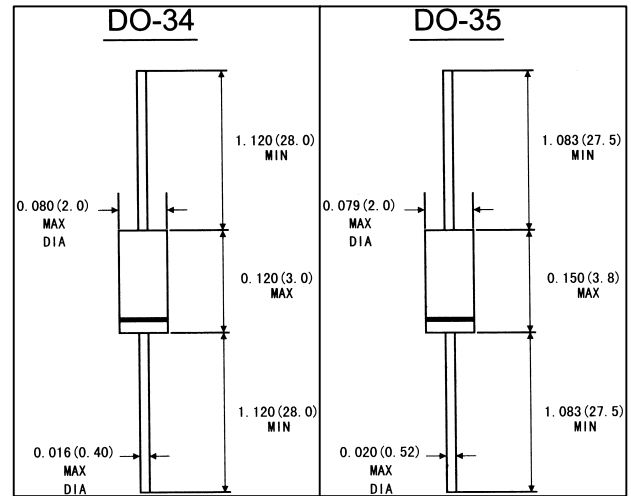


### FEATURES

- Silicon epitaxial planar diode
- Fast switching diodes
- 1N4149, 1N4447, 1N4449 are also available in glass case DO-34

### MECHANICAL DATA

- **Case:** DO-35 glass case
- **Polarity:** Color brand denotes cathode end
- **Weight:** Approx. 0.13gram



Dimensions in inches and (millimeters)

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Type	Peak reverse voltage VRM(V)	Max. Aver. Rectified Current I(AV)Ma	Max. Power Dissip At 25°C Ptot(mW)	Max. Junction temperature TJ °C	Max. Forward Voltage drop		Max. Reverse Current		Max. Reverse Recovery Time	
					VF (V)	at IF (mA)	IR (nA)	at VR(V)	trr(ns) Max.	Test conditions
1N914	100	75	500	200	1.0	10	25	20	4.0	IF=10mA, VR=6V, RL=100Ω, to IR=1mA
1N4149 <sub>1)</sub>	100	150	500	200	1.0	10	25	20	4.0	IF=10mA, VR=6V, RL=100Ω to IR=1mA
1N4150	50	200	500	200	1.0	200	100	50	4.0	IF=IR=10 to 200mA, to 0.1 IF
1N4152	40	150	400	175	0.55	0.10	50	30	2.0	IF=10mA, VR=6V, RL=100Ω to IR=1mA
1N4153	75	150	400	175	0.55	0.10	50	50	2.0	IF=10mA, VR=6V, RL=100Ω to IR=1mA
1N4154	35	150 <sub>2)</sub>	500	200	1.0	0.10	100	25	2.0	IF=10mA, VR=6V, RL=100Ω to IR=1mA
1N4447 <sub>1)</sub>	100	150	500	200	1.0	20	25	20	4.0	IF=10mA, VR=6V, RL=100Ω to IR=1mA
1N4449 <sub>1)</sub>	100	150	500	200	1.0	30	25	20	4.0	IF=10mA, VR=6V, RL=100Ω to IR=1mA
1N4450	40	150	400	175	0.54	0.50	50	30	4.0	IF=IR=10mA to, IR=1mA
1N4451	40	150	400	175	0.50	0.10	50	30	10	IF=IR=10mA to, IR=1mA
1N4453	30	150	400	175	0.55	0.01	50	20		
1N4454	75	150	400	175	1.0	10	100	50	4.0	IF=IR=10mA to, IR=1mA

Notes: 1. These diodes are also available in glass case DO-34

2. Valid provided that leads at a distance of 8mm from case are kept at ambient temperature parameters for diodes

in case DO-34: Ptot=300mW Tstg=-65 to +175°C TJ=175°C RθJA=400K/W